AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application.

1.-15. (Cancelled)

16. (Currently Amended) A method comprising:

applying a photoresist layer to a first substrate to protect [[an active]] a portion having a first circuit;

etching a portion of the first substrate that is not protected by the photoresist layer;

bonding the first substrate to a second substrate after said etching; and thinning the first substrate to remove [[an unsupported]] a bevel portion of the first substrate.

- 17. (Currently Amended) The method of claim 16, wherein said etching comprises etching a curved portion that extends beyond a flat portion having the [[active portion]] first circuit, the curved portion curved so that it would not have been supported by the second substrate when the first and second substrates were bonded.
- 18. (Previously Presented) The method of claim 16, wherein said applying comprises applying the photoresist layer to a wafer.

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- 19. (Currently Amended) The method of claim 16, wherein said bonding comprises bonding the [[active]] portion of the first substrate <u>having the first circuit</u> to the second substrate.
- 20. (Previously Presented) The method of claim 16, wherein said bonding comprises bonding the first substrate to a second substrate having a second circuit.
- 21. (Previously Presented) The method of claim 16, further comprising stripping the photoresist layer after said etching.
- (Previously Presented) The method of claim 16, wherein said etching comprises dry etching.
- (Previously Presented) The method of claim 16, wherein said etching comprises wet etching.
- 24. (Previously Presented) The method of claim 16, wherein said thinning comprises grinding the first substrate.
- 25. (Previously Presented) The method of claim 16, wherein said applying comprises applying the photoresist layer to a flat area just before a curved area.
- 26. (Currently Amended) A method comprising:

removing a first portion of [[an unsupported component from]] a first substrate that is not [[having]] an active component;

bonding the active component of the first substrate to a second substrate; and

thinning the first substrate to remove [[a second portion of the]] an unsupported component of the first substrate.

Attorney Docket No. 42P17268 Application No. 10/811,758 27. (Currently Amended) The method of claim 26, wherein said removing the first

portion [[of the unsupported component]] comprises:

applying a photoresist layer to cover the active component of the first substrate;

and

etching the first portion [[of the unsupported component]] of the first substrate.

28. (Currently Amended) The method of claim 26, wherein said removing the first

portion [[of the unsupported component]] comprises etching a curved portion that

extends beyond a flat portion having the active [[portion]] component, the curved

portion curved so that it would not have been supported by the second substrate

when the first and second substrates were bonded.

29. (Previously Presented) The method of claim 26, wherein said bonding comprises

bonding wafers.

30. (Previously Presented) The method of claim 26, wherein said bonding comprises

bonding the active component of the first substrate to a second substrate having a

circuit.

31. (Previously Presented) The method of claim 26, wherein said thinning the first

substrate comprises grinding the first substrate.

32. (Currently Amended) A method comprising:

forming a layer over a first circuit [[in an active portion]] of a first substrate;

removing a portion of the first substrate that is not under the layer;

removing the layer;

Attorney Docket No. 42P17268 Application No. 10/811,758 bonding the [[active portion]] first circuit of the first substrate to a second substrate having a second circuit after said removing the layer; and

thinning the first substrate to remove a portion that is not supported by the second substrate.

- 33. (Currently Amended) The method of claim 32, wherein said removing the portion of the first substrate comprises removing a curved portion that extends beyond a flat portion having the [[active portion]] first circuit, the curved portion curved so that it would not have been supported by the second substrate when the first and second substrates are bonded.
- 34. (Previously Presented) The method of claim 32, wherein said forming comprises applying a photoresist layer to a wafer.
- 35. (Previously Presented) The method of claim 32, wherein said removing the portion of the first substrate comprises etching the first substrate, wherein said. removing the layer comprises stripping the layer, and wherein said thinning the first substrate comprises grinding the first substrate.
- 36. (New) The method of claim 16, wherein the portion having the first circuit comprises an active portion, and wherein the bevel portion comprises an unsupported portion.
- 37. (New) The method of claim 32, wherein the first circuit is in an active portion of the first substrate.